

# D10XB60HT

**PRV : 600 Volts**  
**Io : 10 Amperes**

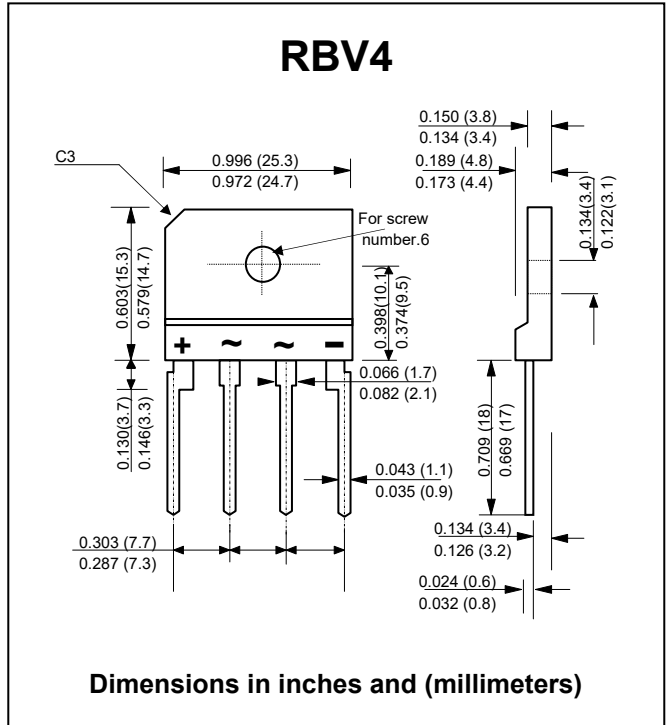
**FEATURES :**

- \* Glass passivated junction chip
- \* High current capability
- \* High surge current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* Ideal for printed circuit board
- \* Very good heat dissipation
- \* **Pb / RoHS Free**

**MECHANICAL DATA :**

- \* Case : Reliable low cost construction utilizing molded plastic technique
- \* Epoxy : UL94V-O rate flame retardant
- \* Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Polarity symbols marked on case
- \* Mounting position : Any
- \* Weight : 4.28 grams

# SILICON BRIDGE RECTIFIER



**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Rating at 25 °C ambient temperature unless otherwise specified.

RATING	SYMBOL	VALUE	UNIT
Maximum Peak Reverse Voltage	$V_{RM}$	600	V
Maximum Average Forward Current (50Hz Sine wave, R-load )	$I_o$	10 3	A
Maximum Peak Forward Surge Current, $T_j = 25\text{ }^\circ\text{C}$ (50Hz sine wave, Non-repetitive 1 cycle peak value)	$I_{FSM}$	120	A
Current Squared Time at $1\text{ms} \leq t < 10\text{ms}$ , $T_j = 25\text{ }^\circ\text{C}$	$I^2t$	60	$A^2S$
Maximum Forward Voltage per Diode at $I_F = 5.0\text{ A}$ ( Pulse measurement, Rating of per diode)	$V_F$	1.1	V
Maximum DC Reverse Current, $V_R = V_{RM}$ ( Pulse measurement, Rating of per diode)	$I_R$	10	$\mu\text{A}$
Maximum Thermal Resistance, Junction to case, With heatsink	$R_{\theta JC}$	2.3	$^\circ\text{C/W}$
Maximum Thermal Resistance, Junction to Ambient, Without heatsink	$R_{\theta JA}$	26	$^\circ\text{C/W}$
Maximum Thermal Resistance, Junction to Lead, Without heatsink	$R_{\theta JL}$	6	$^\circ\text{C/W}$
Operating Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	- 40 to + 150	$^\circ\text{C}$

### RATING AND CHARACTERISTIC CURVES ( D10XB60HT )

FIG.1 - DERATING CURVE

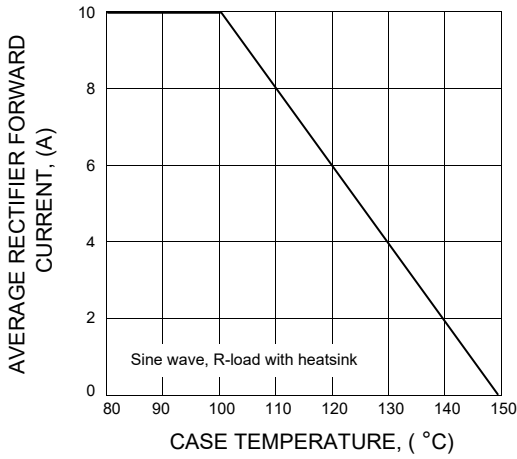


FIG.2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

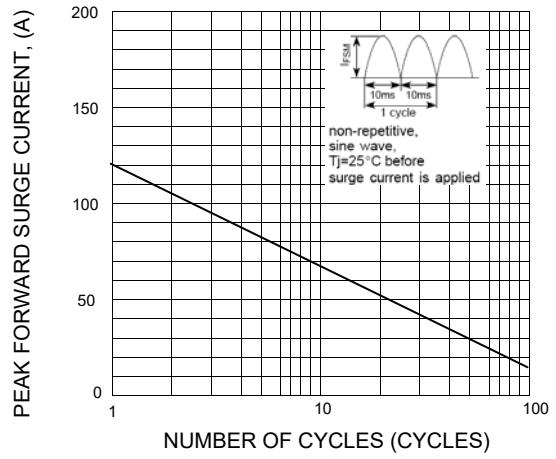


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

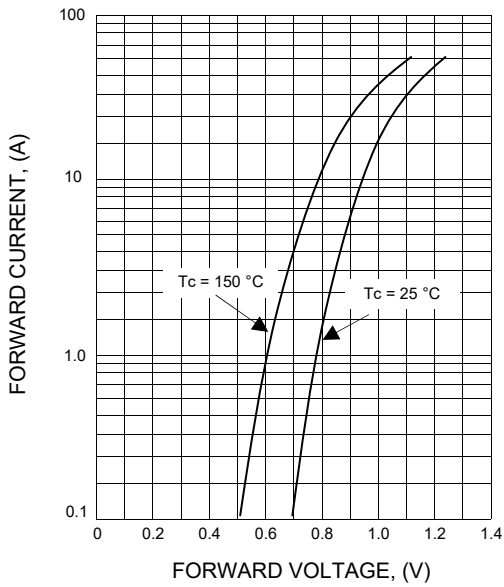


FIG.4 - POWER DISSIPATION

